

A²
5. (Amended) The method for fabricating semiconductor devices according to claim 3, wherein said etching process is performed by setting the processing plasma pressure to below

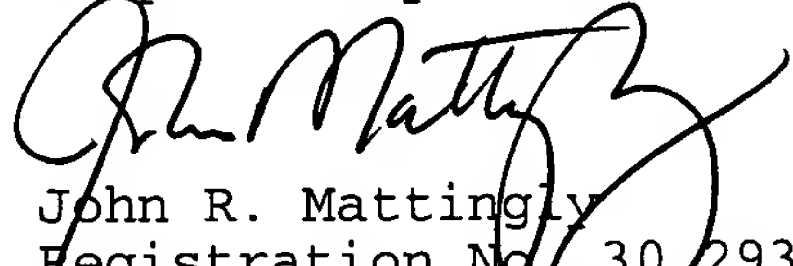
Sub B2
0.5Pa.

6. (Amended) The method for fabricating semiconductor devices according to claim 3, further comprising, immediately after said etching process, a process for subjecting to said sample an O₂ or H₂ plasma processing.

REMARKS

Examination is requested.

Respectfully submitted,


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MARKED UP VERSION OF REWRITTEN CLAIMS

3. (Amended) The method for fabricating semiconductor devices according to claim 1 [or 2], further comprising, after said third step and before said fourth step, an etching process for removing predetermined part of said first insulating material layer by etching by means of plasma of a mixed gas containing NF_3 and Ar through an opening patterned in said second insulating material layer in said third step.

5. (Amended) The method for fabricating semiconductor devices according to claim[s] 3 [or 4], wherein said etching process is performed by setting the processing plasma pressure to below 0.5Pa.

6. (Amended) The method for fabricating semiconductor devices according to [any one of] claim[s] 3 [to 5], further comprising, immediately after said etching process, a process for subjecting to said sample an O_2 or H_2 plasma processing.